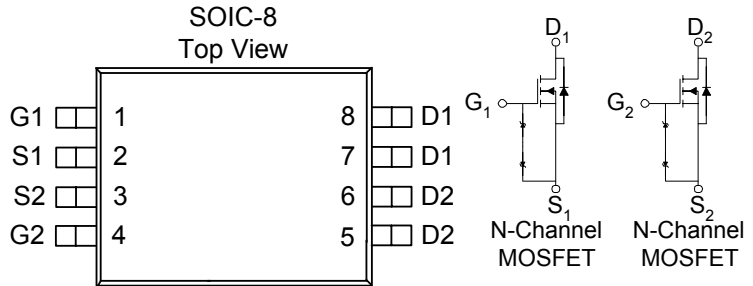


## N-Channel 60-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY		
$V_{DS}$ (V)	$r_{DS(on)}$ m( $\Omega$ )	$I_D$ (A)
60	35 @ $V_{GS} = 10V$	$\pm 6.4$
	45 @ $V_{GS} = 4.5V$	$\pm 5.6$

- Low  $r_{DS(on)}$  provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		$V_{DS}$	60	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current <sup>a</sup>	$T_A = 25^\circ\text{C}$	$I_D$	$\pm 6.4$	A
	$T_A = 70^\circ\text{C}$		$\pm 5.2$	
Pulsed Drain Current <sup>b</sup>		$I_{DM}$	$\pm 40$	
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	2	A
Power Dissipation <sup>a</sup>	$T_A = 25^\circ\text{C}$	$P_D$	2.1	W
	$T_A = 70^\circ\text{C}$		1.3	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS				
Parameter		Symbol	Maximum	Units
Maximum Junction-to-Ambient <sup>a</sup>	$t \leq 10 \text{ sec}$	$R_{\theta JA}$	62.5	$^\circ\text{C/W}$
	Steady State		110	$^\circ\text{C/W}$

### Notes

- Surface Mounted on 1" x 1" FR4 Board.
- Pulse width limited by maximum junction temperature

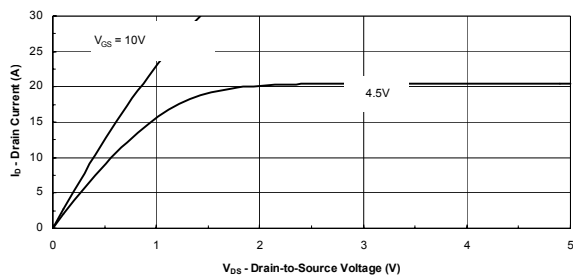
SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min	Typ	Max	
Static						
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 uA	1			
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 20 V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	uA
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55°C			10	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 10 V	20			A
Drain-Source On-Resistance <sup>A</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 6.4 A			35	mΩ
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 5.6 A			45	
Forward Tranconductance <sup>A</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 6.4 A		11		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = 2.0 A, V <sub>GS</sub> = 0 V			1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 6.4 A		12.5		nC
Gate-Source Charge	Q <sub>gs</sub>			2.4		
Gate-Drain Charge	Q <sub>gd</sub>			2.6		
Switching						
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = 30 V, R <sub>L</sub> = 30 Ω , I <sub>D</sub> = 1 A , V <sub>GEN</sub> = 10 V		11		nS
Rise Time	t <sub>r</sub>			8		
Turn-Off Delay Time	t <sub>d(off)</sub>			19		
Fall-Time	t <sub>f</sub>			6		

## Notes

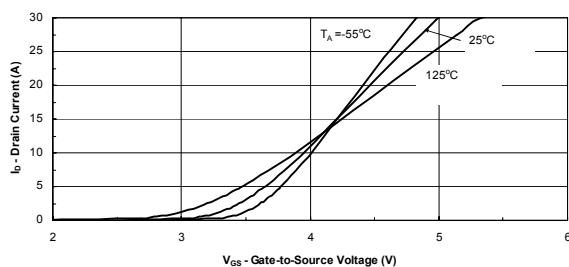
- Pulse test: PW ≤ 300µs duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.

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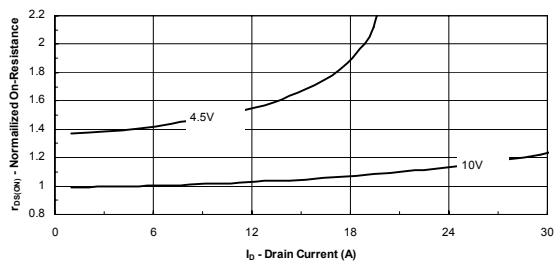
## Typical Electrical Characteristics



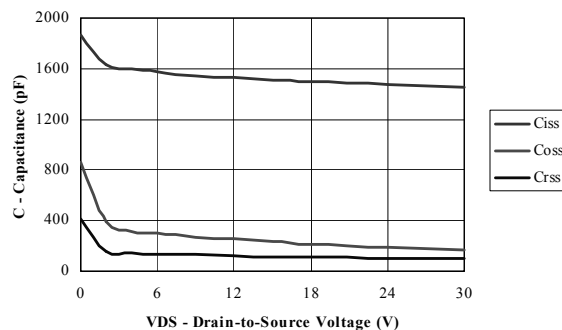
Output Characteristics



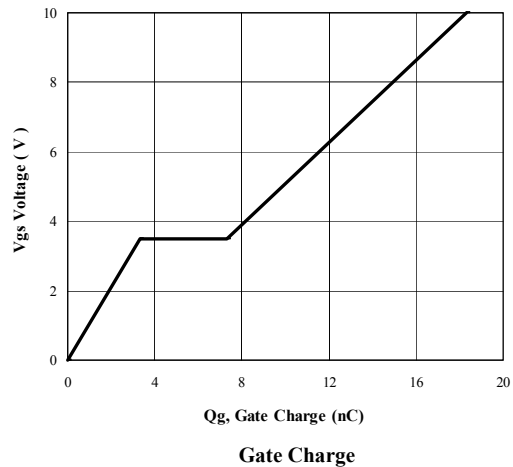
Transfer Characteristics



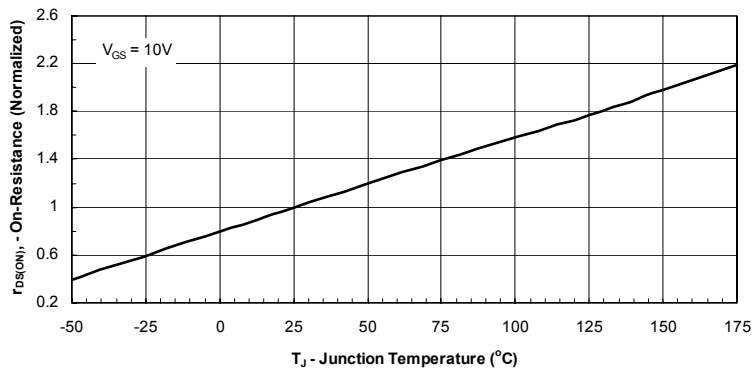
On-Resistance vs. Drain Current



Capacitance

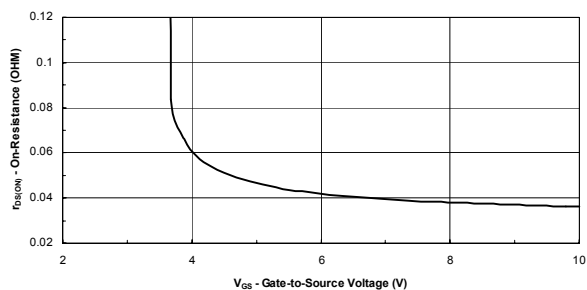
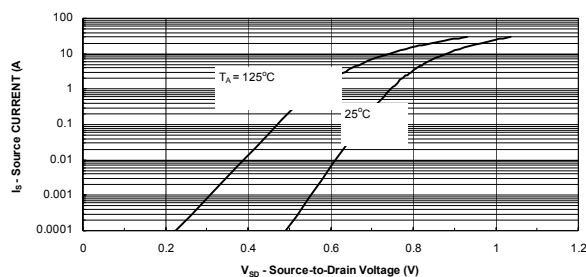


Gate Charge

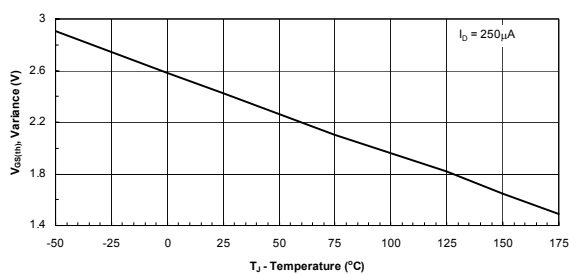


On-Resistance vs. Junction Temperature

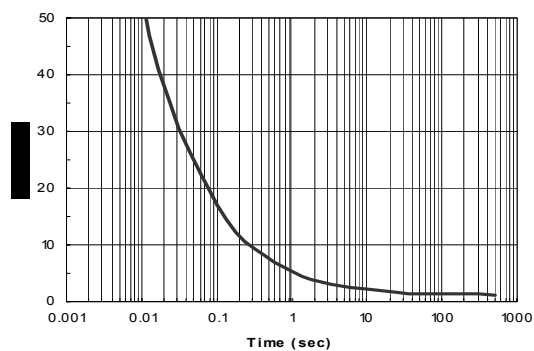
## Typical Electrical Characteristics (N-Channel)



Source-Drain Diode Forward Voltage

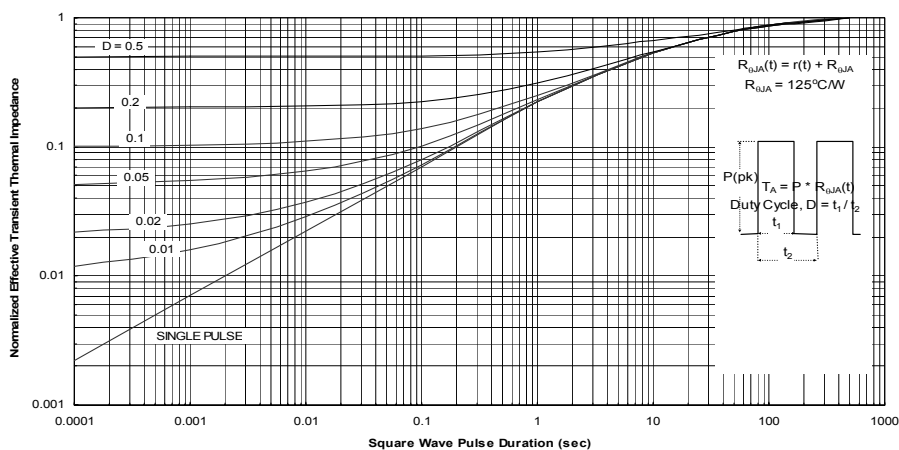


On-Resistance vs. Gate-to Source Voltage



Threshold Voltage

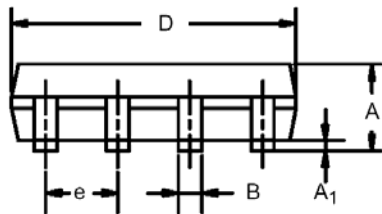
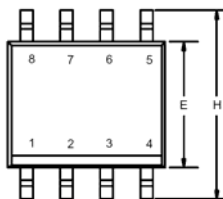
Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

Package Information

SO-8: 8LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°

